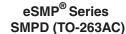
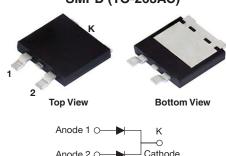


# Hyperfast Rectifier, 2 x 10 A FRED Pt®





#### **DESIGN SUPPORT TOOLS AVAILABLE**



| PRIMARY CHARACTERISTICS          |                 |  |  |  |
|----------------------------------|-----------------|--|--|--|
| I <sub>F(AV)</sub>               | 2 x 10 A        |  |  |  |
| V <sub>R</sub>                   | 200 V           |  |  |  |
| V <sub>F</sub> at I <sub>F</sub> | 0.77 V          |  |  |  |
| t <sub>rr</sub>                  | 25 ns           |  |  |  |
| T <sub>J</sub> max.              | 175 °C          |  |  |  |
| Package                          | SMPD (TO-263AC) |  |  |  |
| Circuit configuration            | Common cathode  |  |  |  |

#### **FEATURES**

 Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery



RoHS

COMPLIANT HALOGEN

FREE

- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- zon formara voltago aro,
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, telecom, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

| ABSOLUTE MAXIMUM RATINGS          |            |                    |   |        |       |
|-----------------------------------|------------|--------------------|---|--------|-------|
| PARAMETER                         |            | SYMBOL             | TEST CONDITIONS                           | VALUES | UNITS |
| Peak repetitive reverse voltage   |            | $V_{RRM}$          |   | 200    | V     |
| Average rectified forward current | per device | I <sub>F(AV)</sub> | T <sub>solder pad</sub> = 152 °C          | 20     |       |
| Average rectilled forward current | per diode  |                    |   | 10     | ۸     |
|                                   | per device |                    | T <sub>J</sub> = 25 °C, 6 ms square pulse | 210    | А     |
| Non-repetitive peak surge current | per diode  | IFSM               |   | 110    |       |

| <b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |  |   |      |      |      |       |
|--|--|---|------|------|------|-------|
| PARAMETER  | SYMBOL   | TEST CONDITIONS                                       | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage,<br>blocking voltage   | V <sub>BR</sub> ,<br>V <sub>R</sub>            | I <sub>R</sub> = 100 μA                               | 200  | -    | -    |       |
| Forward voltage, per diode V <sub>F</sub>  | V-   | I <sub>F</sub> = 10 A                                 | -    | 0.94 | 1.05 | V     |
|  | I <sub>F</sub> = 10 A, T <sub>J</sub> = 150 °C | -   | 0.77 | 0.87 |      |       |
| D  |  | V <sub>R</sub> = V <sub>R</sub> rated                 | -    | -    | 2    |       |
| Reverse leakage current, per diode I <sub>R</sub>                                    |  | $T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{ rated}$ | -    | 10   | 150  | μΑ    |
| Junction capacitance, per diode  | C <sub>T</sub>                                 | V <sub>R</sub> = 200 V                                | -    | 30   | -    | pF    |



| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                  |  |  |      |      |      |       |
|---|------------------|--|--|------|------|------|-------|
| PARAMETER   | SYMBOL           | TEST CONDITIONS                                  |  | MIN. | TYP. | MAX. | UNITS |
|   |                  | I <sub>F</sub> = 1 A, dI <sub>F</sub> /dt = 50 A | õs, V <sub>R</sub> = 30 V  | -    | 25   | -    |       |
| Reverse recovery time   |                  | $I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr}$ | = 0.25 A   | -    | -    | 25   | ns    |
| neverse recovery time   | t <sub>rr</sub>  | T <sub>J</sub> = 25 °C                           |  | -    | 22   | -    |       |
|   |                  | T <sub>J</sub> = 125 °C                          |  | -    | 35   | -    |       |
| Peak recovery current   | l                | T <sub>J</sub> = 25 °C                           | $I_F = 10 \text{ A},$<br>$dI_F/dt = 200 \text{ A/}\mu\text{s},$<br>$V_R = 160 \text{ V}$ | -    | 2.5  | -    | - A   |
| reak recovery current   | I <sub>RRM</sub> | T <sub>J</sub> = 125 °C                          |  | -    | 5    | -    |       |
| Daversa rasavan raharra   | 0                | T <sub>J</sub> = 25 °C                           |  | -    | 25   | -    | nC    |
| Reverse recovery charge   | $Q_{rr}$         | T <sub>J</sub> = 125 °C                          |  | -    | 85   | -    | IIC   |

| THERMAL - MECHANICAL SPECIFICATIONS                  |                                   |                            |      |      |      |       |
|--|-----------------------------------|----------------------------|------|------|------|-------|
| PARAMETER  | SYMBOL                            | TEST CONDITIONS            | MIN. | TYP. | MAX. | UNITS |
| Maximum junction and storage temperature range       | T <sub>J</sub> , T <sub>Stg</sub> |                            | -55  | -    | +175 | °C    |
| Thermal resistance, per diode junction to solder pad | R <sub>thJ-Sp</sub>               |                            | -    | 1.8  | 2.4  | °C/W  |
| Approximate weight                                   |                                   |                            |      | 0.55 |      | g     |
| Approximate weight                                   |                                   |                            |      | 0.02 |      | oz.   |
| Marking device                                       |                                   | Case style SMPD (TO-263AC) |      | 20CI | DH02 |       |

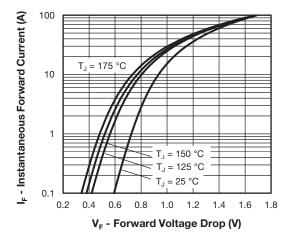


Fig. 1 - Typical Forward Voltage Drop Characteristics

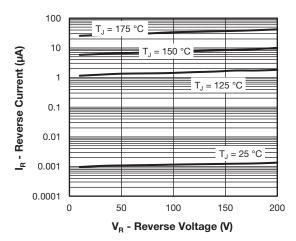


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

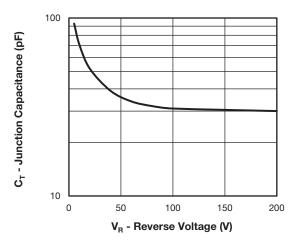


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

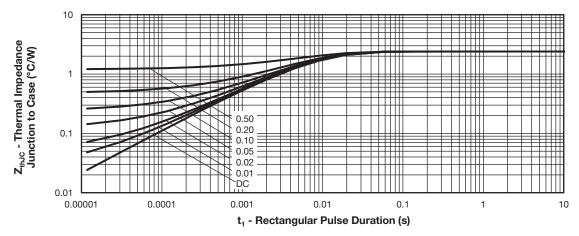


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

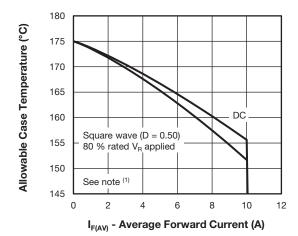


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

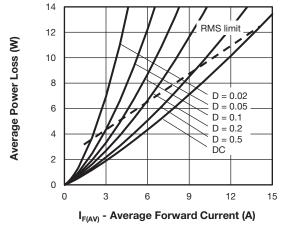


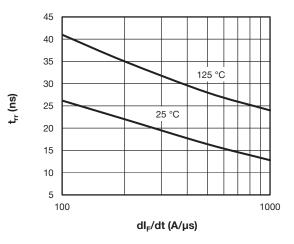
Fig. 6 - Forward Power Loss Characteristics

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;  $Pd = forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$  (see fig. 5);  $Pd_{REV} = inverse power loss = V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1} = rated V_R$ 

#### www.vishay.com

## Vishay Semiconductors





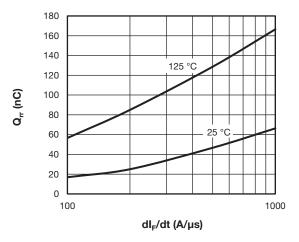
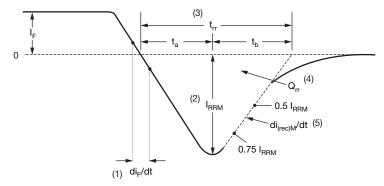


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_{F}$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

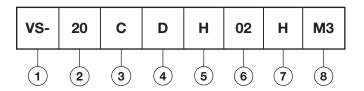
(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions



### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

Current rating (20 A)

Circuit configuration:

C = common cathode

4 - D = SMPD package

5 - Process type,

H = hyperfast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

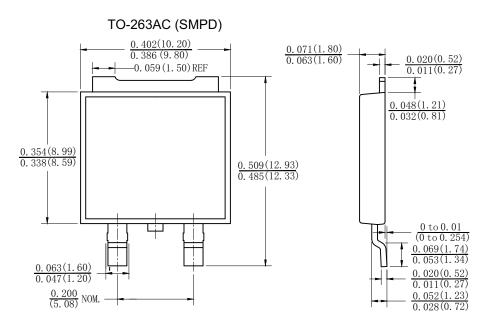
| ORDERING INFORMATION (Example) |                   |                        |                                    |  |  |
|--------------------------------|-------------------|------------------------|------------------------------------|--|--|
| PREFERRED P/N                  | QUANTITY PER REEL | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION              |  |  |
| VS-20CDH02HM3/I                | 2000              | 2000                   | 13" diameter plastic tape and reel |  |  |

| LINKS TO RELATED DOCUMENTS |                          |  |  |  |
|----------------------------|--------------------------|--|--|--|
| Dimensions                 | www.vishay.com/doc?95604 |  |  |  |
| Part marking information   | www.vishay.com/doc?95566 |  |  |  |
| Packaging information      | www.vishay.com/doc?88869 |  |  |  |
| SPICE model                | www.vishay.com/doc?96572 |  |  |  |

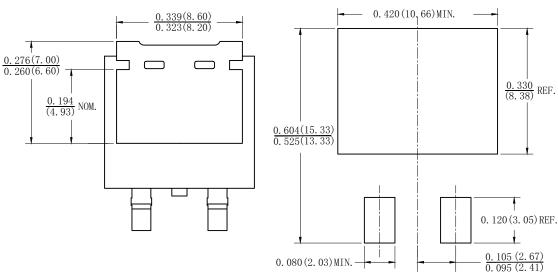


# TO-263AC (SMPD)

### **DIMENSIONS** in inches (millimeters)



### Mounting Pad Layout





### **Legal Disclaimer Notice**

Vishay

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